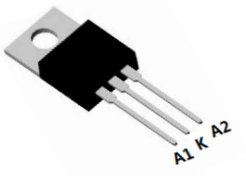
WSB20L100T

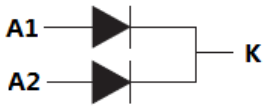
Power Schottky Barrier Rectifier

www.sh-willsemi.com

Features

- 2x10A average rectified forward current
- Low forward voltage and Low leakage current
- High Junction temperature
- High forward and reverse Surge capability

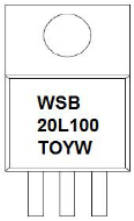




Circuit

Applications

- High frequency switch model power supplies
- DC-DC Convertors, Power adapters



WSB20L100 = Device code
TO = Special code
Y =Year
W =Week（A~z）

Marking

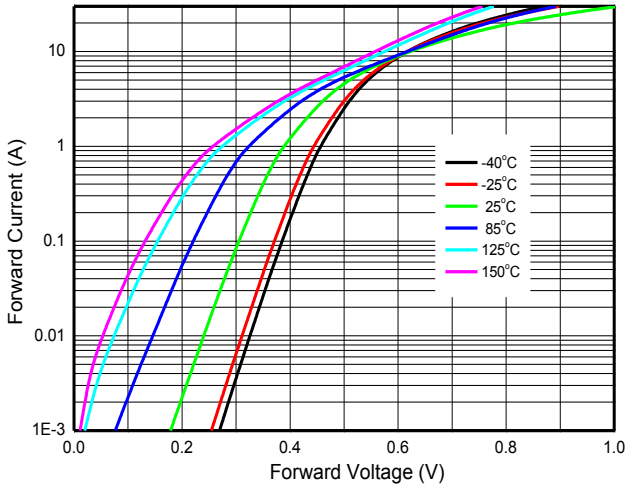
Absolute maximum ratings				
Parameter		**Symbol**	**Value**	**Unit**
Reverse voltage (repetitive peak)		V_{RM}	100	V
Reverse voltage (DC)		V_R	100	V
Average rectified forward current	Per diode	I_F	10	A
	Per device	I_F	20	A
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave		I_{FSM}	200	A
Junction temperature		T_J	150	^{0}C
Operating temperature		Topr	-55 ~ 150	^{0}C
Storage temperature		Tstg	-55 ~ 150	^{0}C
Thermal Resistance Ratings				
Maximum Thermal Resistance Junction To case (Per leg)	TO-220	$R_{\theta JC}$	2.0	°C/W

Order information			
Device	**Package**	**Marking**	**Units/Tube**
WSB20L100T-3/T	TO-220	WSB20L100TOYW	50

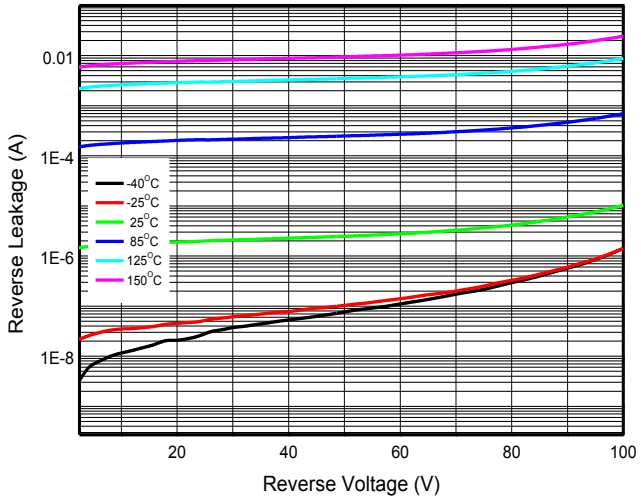
Electronics characteristics (Per diode, T_A =25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage	V_R	I_R=0.5mA	100			V
Forward voltage	V_F	I_F=10A		0.6	0.7	V
Reverse current	I_R	V_R=100V	-	11	100	uA
Junction capacitance	C_J	V_R=25V, F=1MHz	-	180		pF

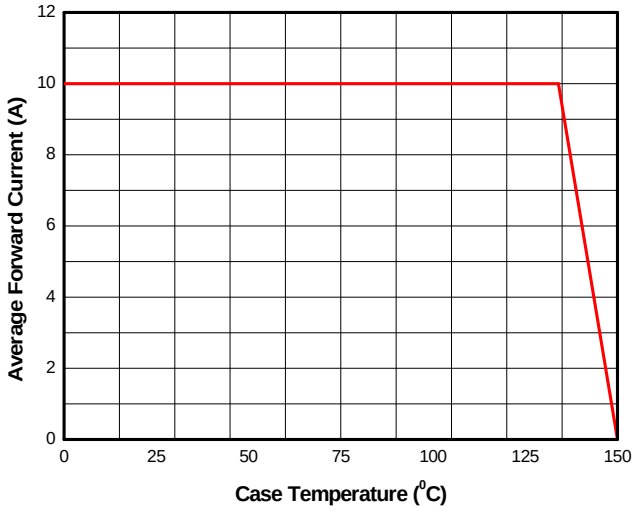
Typical characteristics (Ta=25°C, unless otherwise noted)



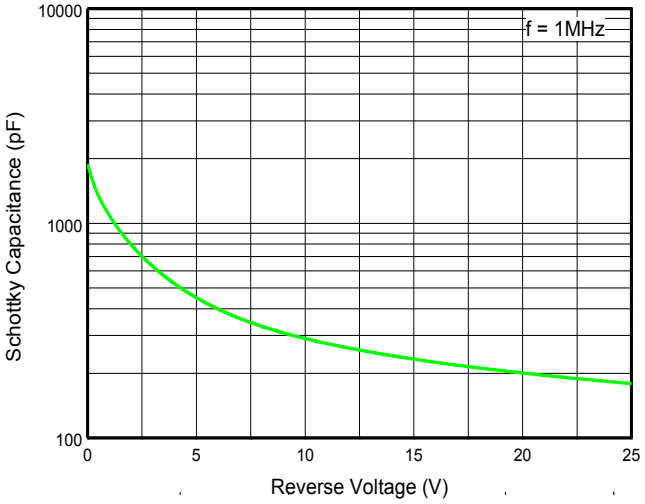
Forward voltage vs. Forward current



Reverse current vs. Reverse voltage



Forward Current Derating Curve



Junction capacitance vs. Reverse voltage

Package outline dimensions

TO-220